

	Hits	Search Text	DBs
2	261	((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4)) and post\$8expos\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and (metal\$4 or conductiv\$3 or TFT or LCD or (gate near6 electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
3	87	((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4)) and post\$8expos\$4 and (etch\$4 or RIE or (dry near5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
4	34	((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (multiple or plurali\$4 or dual or double or second) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4) same (expos\$4 or illuminat\$4 or irradiat\$4)) and (post\$8imag\$4 or post\$5expos\$3) and (etch\$4 or RIE or (dry near5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
5	65	((resist or photoresist or photosensitive or radiation\$5sensitive) same (expos\$4 or irradiat\$4 or illuminat\$4) same (photosensiti\$5 or diazonaphthoquinone) same develop\$4) and ((resist or photoresist or photosensitive) same pattern\$4 same (strip\$4 or remov\$4) same (expos\$4 or illuminat\$4 or irradiat\$4)) and (post\$8imag\$4 or post\$5expos\$3) and (etch\$4 or RIE or (dry near5 etch\$4)) and ((metal\$4 or conductiv\$3 or TFT or LCD or (gate near6 electrode)) same (substrate or wafer) same (resist or photoresist) same (pattern\$4 or mask) same (post\$4etch\$4 or etch\$3 or RIE or (dry near4 etch\$4)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB